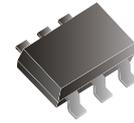


CDSV6-99SD-G

Reverse Voltage: 75 Volts
Forward Current: 215 mA
RoHS Device



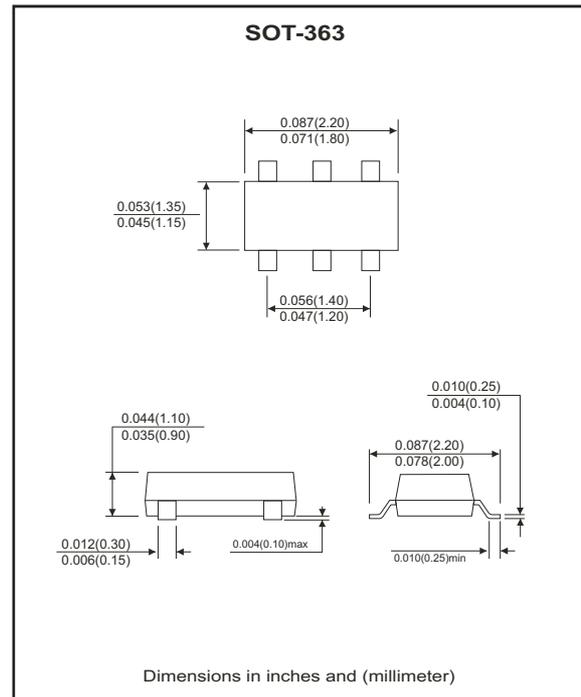
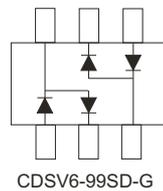
Features

- Design for mounting on small surface.
- High speed switching.
- Ultra small surface mount package.
- Two BAV99 circuits in one package.

Mechanical data

- Case: SOT-363, molded plastic.
- Terminals: solderable per MIL-STD-750, method 2026.
- Approx. weight: 0.006 grams

Circuit diagram



Maximum Ratings and Electrical Characteristics

(at Ta=25 °C unless otherwise noted)

Parameter	Symbol	Conditions	Value	Units
Repetitive peak reverse voltage	V _{RRM}		75	V
Reverse voltage	V _R		75	V
Forward current	I _F		215	mA
Peak surge forward current	I _{FSM}	T=1.0 μS	2	A
Power dissipation	P _D		200	mW
Maximum forward voltage	V _F	@I _F =1mA @I _F =10mA @I _F =50mA @I _F =100mA	0.715 0.855 1.0 1.25	V
Maximum reverse current	I _R	@V _R =20V @V _R =75V @V _R =25V, T _J =150 °C @V _R =75V, T _J =150 °C	0.025 2.5 30 50	μA
Maximum reverse recovery time	T _{rr}	I _F =I _R =10mA, R _L =100Ω	4	nS
Typical diode capacitance	C _T	V _R =0V, f=1.0MHz	2	pF
Maximum junction temperature	T _J		150	°C
Storage temperature	T _{STG}		-55 to +150	°C

RATING AND CHARACTERISTIC CURVES (CDSV6-99SD-G)

Fig.1 - Forward Characteristics

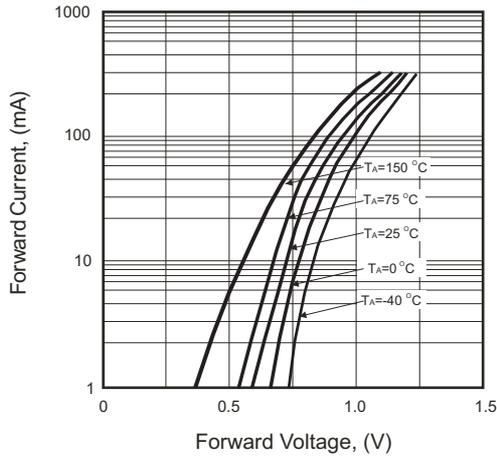


Fig.2 - Reverse Characteristics

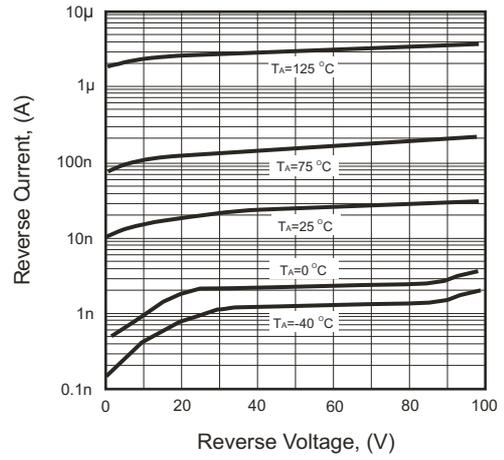


Fig.3 - Capacitance Between Terminals Characteristics

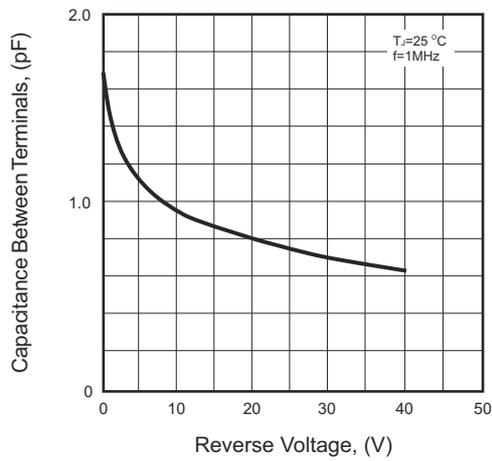


Fig.4 - Power Derating Curve

